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VAN HOVE SINGULARITY AND SUPERCONDUCTIVITY IN DISORDERED Sr_2RuO_4

G. LITAK^a, J.F. ANNETT^b AND B.L. GYÖRFFY^b

 Department of Mechanics, Technical University of Lublin Nadbystrzycka 36, 20-618 Lublin, Poland
 H.H. Wills Physics Laboratory, University of Bristol Tyndall Ave, Bristol BS8 1TL, United Kingdom

On the basis of a simple model we analyse the influence of disorder on critical temperature T_c in p-wave superconductors. The disorder is treated by means of the coherent potential approximation and we focus our attention on the effect of a van Hove singularity near Fermi energy $E_{\rm F}$. For the appropriate values of its parameters our model reproduces the experimentally found behaviour of $\rm Sr_2RuO_4$.

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1. Introduction

The perovskite structure of strontium ruthenate, Sr_2RuO_4 is very similar to that of HTS copper oxides. However, its superconducting transition temperature T_c is relatively low ($T_c \approx 1$ K) [1]. Nevertheless, recent reports indicate that its Cooper pairs are not of the usual s-wave symmetry. In fact, they suggest that this material features triplet pairing and is a superconducting analogue of the ³He superfluid system [1–4]. Clearly, the possibility of exotic pairing engenders interest in the effects of disorder on the superconducting properties. Moreover, studies of the electronic structure [2, 3] have identified an extended van Hove singularity close to the Fermi energy E_F , and therefore, one may wonder whether the van Hove scenario could lead to a rise in T_c with doping. Evidently, since doping the system always increases the disorder one should investigate both aspects simultaneously.

2. The model

We base our discussion on the extended negative U Hubbard Hamiltonian

$$H = \sum_{ij\sigma} t_{ij} c_{i\sigma}^{\dagger} c_{j\sigma} + \frac{1}{2} \sum_{ij} U_{ij} \widehat{n}_i \widehat{n}_j - \sum_i (\mu - \varepsilon_i) \widehat{n}_i, \tag{1}$$

where $\hat{n}_i = \hat{n}_{i\uparrow} + \hat{n}_{i\downarrow}$ and $\hat{n}_{i\sigma}$ is the usual, site occupational number operator $c^{\dagger}_{i\sigma}c_{i\sigma}$. Evidently the above \hat{n}_i is the charge operator on a site labelled i, μ is the chemical potential, which at T=0 is equal to Fermi energy $E_{\rm F}$. Disorder is introduced into the problem by allowing the local site energy ε_i to vary randomly from site to site. Finally, $c^{\dagger}_{i\sigma}$ and $c_{i\sigma}$ are the Fermion creation and annihilation operators for

an electron on site i with spin σ , t_{ij} is the amplitude for hopping from site j to site i and U_{ij} is the attractive interaction $(i \neq j)$ which causes superconductivity.

In the Hartree-Fock-Gorkov approximation the equation for the Green function $G(i, j; i\omega_n)$, corresponding to the Hamiltonian in Eq. (1), is given by

$$\sum_{l} \begin{bmatrix} (i\omega_{n} + \mu - \varepsilon_{i})\delta_{il} + t_{il} & \Delta_{il} \\ \Delta_{il}^{*} & (i\omega_{n} - \mu + \varepsilon_{i})\delta_{il} - t_{il} \end{bmatrix} G(l, j; i\omega_{n}) = \mathbf{1}\delta_{ij}, (2)$$

where ω_n is Matsubara frequency. Let us define the random potential V^{ε_i} by

$$\boldsymbol{V}^{\varepsilon_i} = \begin{bmatrix} \varepsilon_i & 0\\ 0 & -\varepsilon_i \end{bmatrix}, \tag{3}$$

where ε_i is uniformly distributed on the energy interval $[-\delta/2, \delta/2]$. The Green function for an impurity, described by $\mathbf{V}^{\varepsilon_i}$ in Eq. (3), embedded in the medium, described by $\mathbf{\Sigma}(\mathrm{i}\omega_n)$ is given by

$$G^{\varepsilon_i}(i, i, i\omega_n) = \{1 - G^{c}(i, i, i\omega_n)[V^{\varepsilon_i} - \Sigma(i\omega_n)]\}^{-1}G^{c}(i, i, i\omega_n).$$
(4)

Following the usual coherent potential approximation (CPA) procedure we demand that the coherent potential Green function $G^{c}(i, i; i\omega_n) = G^{0}(i, i; i\omega_n 1 - \Sigma(i\omega_n))$, where $G^{0}(i, i; i\omega_n)$ is the Green function for the clean system with $\varepsilon_i = 0$ for every site i, satisfies the following relation:

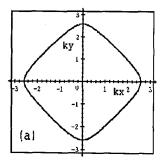
$$\mathbf{G}^{c}(i, i, i\omega_{n}) = \langle \mathbf{G}^{\epsilon_{i}}(i, i, i\omega_{n}) \rangle = \frac{1}{\delta} \int_{-\delta/2}^{\delta/2} d\varepsilon_{i} \, \mathbf{G}^{\epsilon_{i}}(i, i, i\omega_{n}). \tag{5}$$

Evidently, Eq. (5) completely determines that it can be solved for $\Sigma(i\omega_n)$.

Let us now proceed further with the CPA strategy [5] and determine the averaged Green function matrix $\langle G(i,j;i\omega_n)\rangle$ subject to the self-consistency conditions

$$\overline{\Delta}_{ij} = |U_{ij}| \frac{1}{\beta} \sum_{n} \exp(\mathrm{i}\omega_n \eta) \langle G_{12}(i,j;\mathrm{i}\omega_n) \rangle, \ \overline{n} = \frac{2}{\beta} \sum_{n} \exp(\mathrm{i}\omega_n \eta) \langle G_{11}(i,i;\mathrm{i}\omega_n) \rangle. (6)$$

In this paper we assumed nearest neighbour electron hopping and pairing on a two-dimensional lattice. In Fig. 1a and b we have presented Fermi surfaces



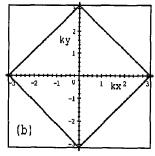


Fig. 1. Fermi surfaces for the one-band electron structure with nearest neighbour hoping: $\epsilon_k = -2t(\cos k_x + \cos k_y)$, and two different band fillings: n = 0.55 (a), n = 1.00 (b).

for n=0.55 and n=1, respectively. The latter case correspond to the situation, where the Fermi energy, $E_{\rm F}$, is located exactly at the van Hove singularity.

3. Critical temperature and residual resistivity

The linearised gap equation for the critical temperature T_c of p-wave superconducting phase transition reads as follows [6]:

$$1 = \frac{|U|T_{c}}{N} \sum_{n,k} \exp\left(i\omega_{n}\eta\right) \frac{2(\sin k_{x})^{2}}{[i\omega_{n} - \epsilon_{k} + \mu - \Sigma_{11}(i\omega_{n})][i\omega_{n} + \epsilon_{k} - \mu - \Sigma_{22}(i\omega_{n})]}. \quad (7)$$

A useful measure of disorder is the resistivity ρ . Thus we shall study the relationship between ρ and T_c . The residual resistivity ρ for low temperature can be obtained from the Kubo-Greenwood formula. For the disordered two-dimensional systems at hand [7]

$$\rho = \left\{ 2 \frac{e^2}{\pi \hbar c} \frac{1}{N} \sum_{\mathbf{k}} 4(\sin k_x)^2 t^2 \left[\text{Im} G_{11}^c(\mathbf{k}, 0) \right]^2 \right\}^{-1}, \tag{8}$$

where e is the electron charge, \hbar is Plank constant and c is the distance between RuO₂ planes. In short, we have solved the CPA equations (Eqs. (4, 5)) for various system parameters (Eq. (1)) and calculated both T_c and residual resistivity ρ .

To illustrate how effective a van Hove singularity can be in raising $T_{\rm c}$, in Fig. 2a we present $T_{\rm c}$, calculated for clean systems and normalised to its maximal value $T_{\rm c}^{\rm max}$, versus band filling n for various values of U/t. Clearly, $T_{\rm c}$ is peaked at n=1, where the Fermi energy $E_{\rm F}$ is exactly at the van Hove singularity. For a small enough interaction U it is enlarged by a factor of 7. Going further we turn to our results for the disordered case. Thus, in Fig. 2b, we plotted $T_{\rm c}$ versus residual resistivity ρ as calculated by the CPA procedure described above. The parameters U/t=-0.702 as well as band filling n=0.55 were chosen so that the $T_{\rm c}$ vs. ρ curve reproduces the experiments [1]. Unlike the Born approximation limit, the CPA residual resistivity is dependent on the strength of disordered potential, δ , nonlinearly. This is illustrated in Fig. 3a, where the different curves correspond

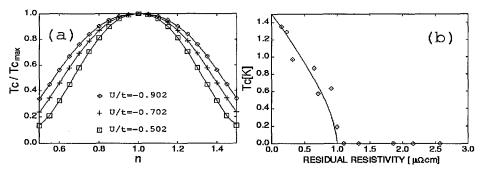


Fig. 2. (a) T_c for the clean system vs. band filling n for various interactions U. (b) T_c vs. residual resistivity fitted for Sr_2RuO_4 . The diamonds are the data of Ref. [1].

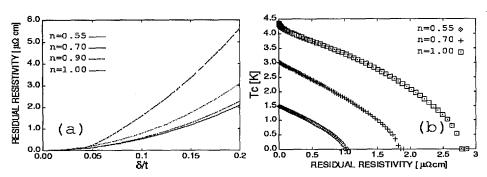


Fig. 3. (a) Residual resistivity vs. strength of disordered potential $\delta(\epsilon; \in [-\delta/2, \delta/2])$ for various band fillings n. (b) T_c vs. residual resistivity for various band fillings n.

to different band fillings n. The pronounced nonlinearity for n=1 is due to a van Hove singularity being near $E_{\rm F}$. As shown in Fig. 3b this gives rise to an interesting upturn as $\rho \to 0$ in the $T_{\rm c}$ vs. ρ plot.

4. Remarks and conclusions

Our results confirm that, similarly to d-wave superconductors [5], in the case of p-wave paring the critical temperature T_c is a very sensitive function of nonmagnetic diagonal disorder. Nevertheless, they suggest that in Sr_2RuO_4 doping could lead to a higher value of critical temperature T_c . Here we used uniform distribution of site energy levels ε_i as the simplest model of disorder. Clearly a further study of the problem would include a more sophisticated impurity model, and a more realistic band structure.

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